

Transient Electronics

- 1) Motivation, Perspective
- 2) Materials, Device Designs, Manufacturing
- 3) Ecoresorbable RFID, Electronic Medicines

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***Louis Simpson and Kimberly Querrey Professor
SQI and Center for Biointegrated Electronics***

The Dominant Future for Electronics: *Smaller, Faster, Cheaper*

Past



Present

Future



Industrial



Personal



***Smaller, Faster
Cheaper***

An Alternative Future for Electronics: Bio / Eco Resorbable, *Transient*

Past



Present



Future



Industrial



Personal



Bio / Eco Resorbable

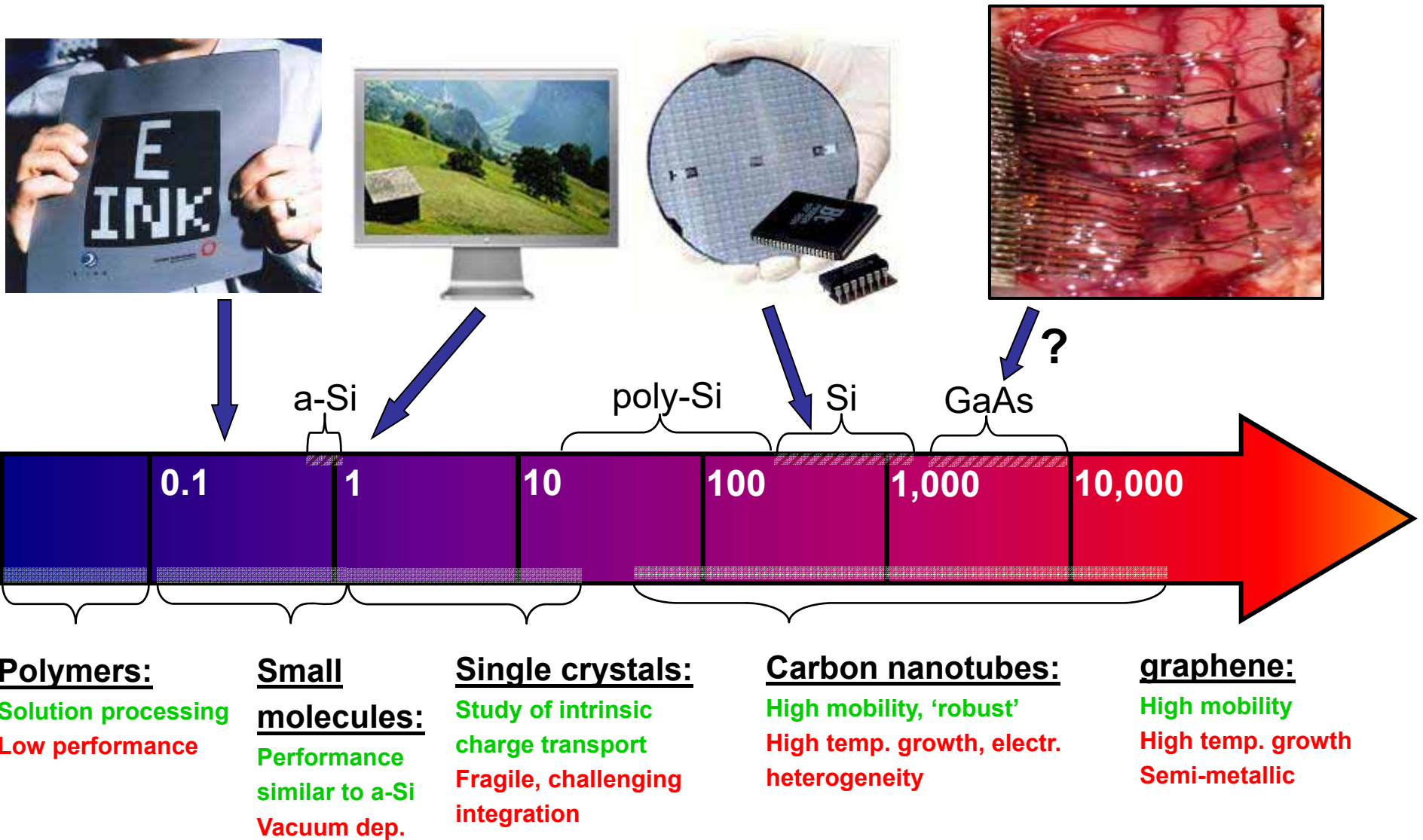
Definition – Transient Electronics

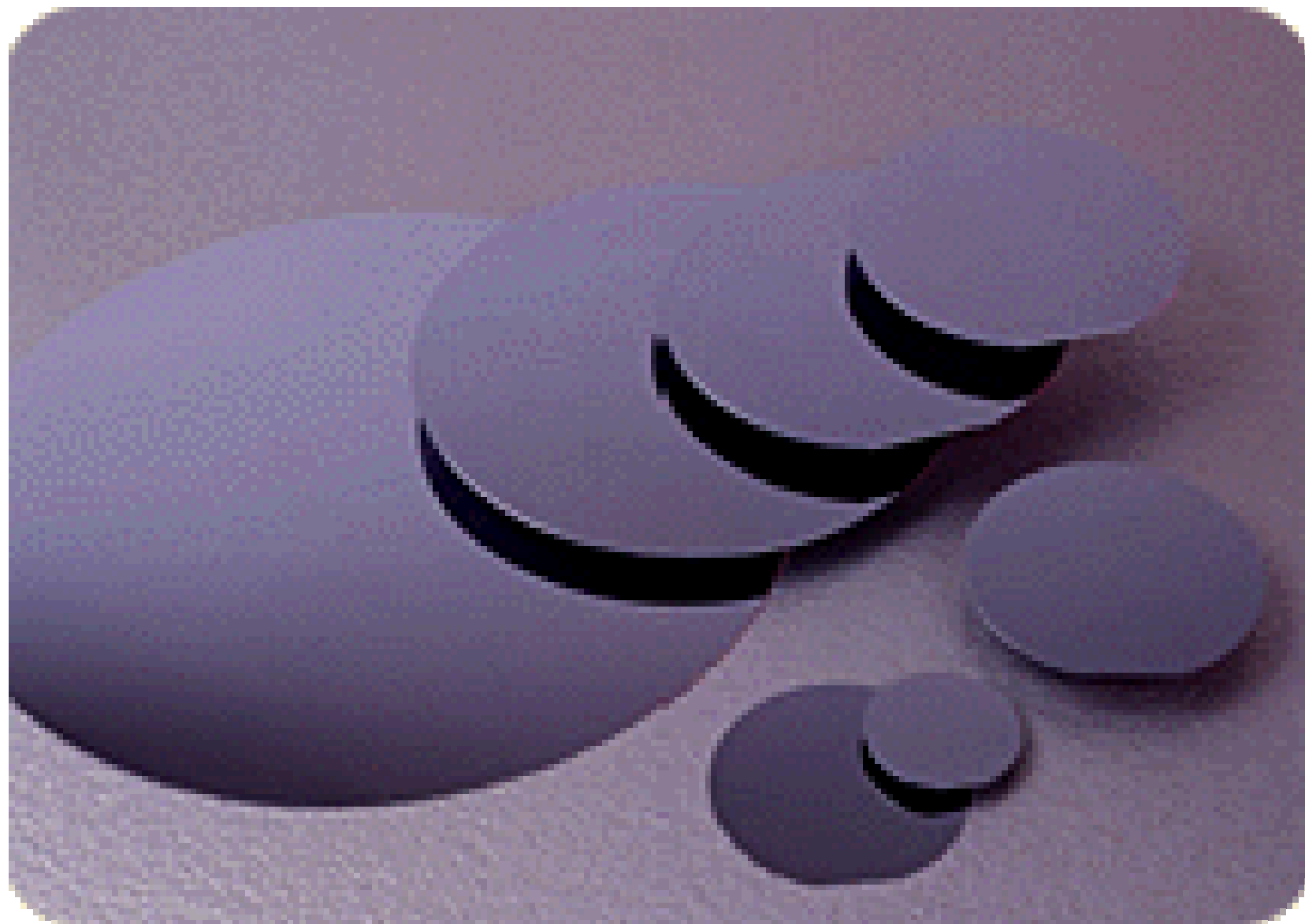
Transient Electronics – electronic systems that dissolve, resorb or otherwise physically disappear at programmed rates or at triggered times

Transient Electronics – Application Opportunities

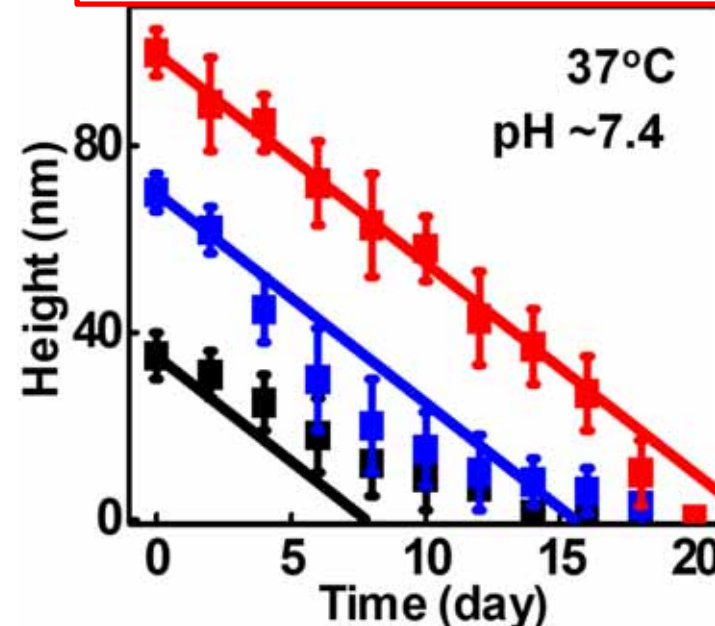
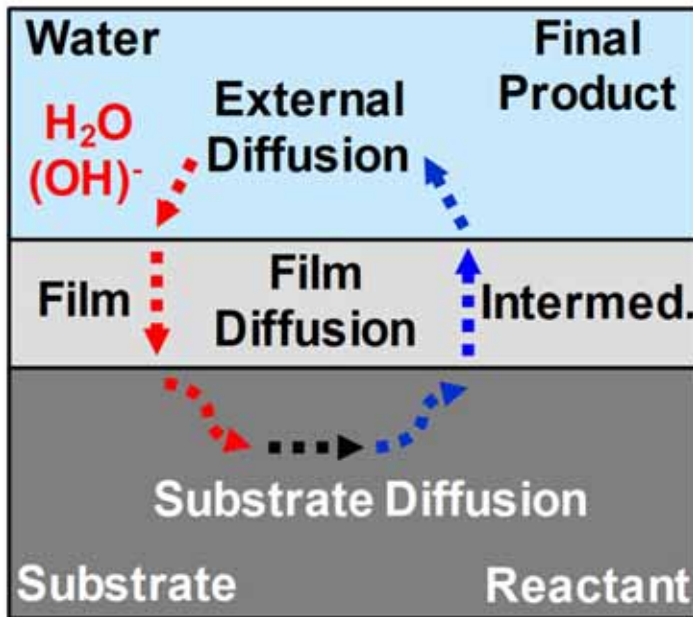
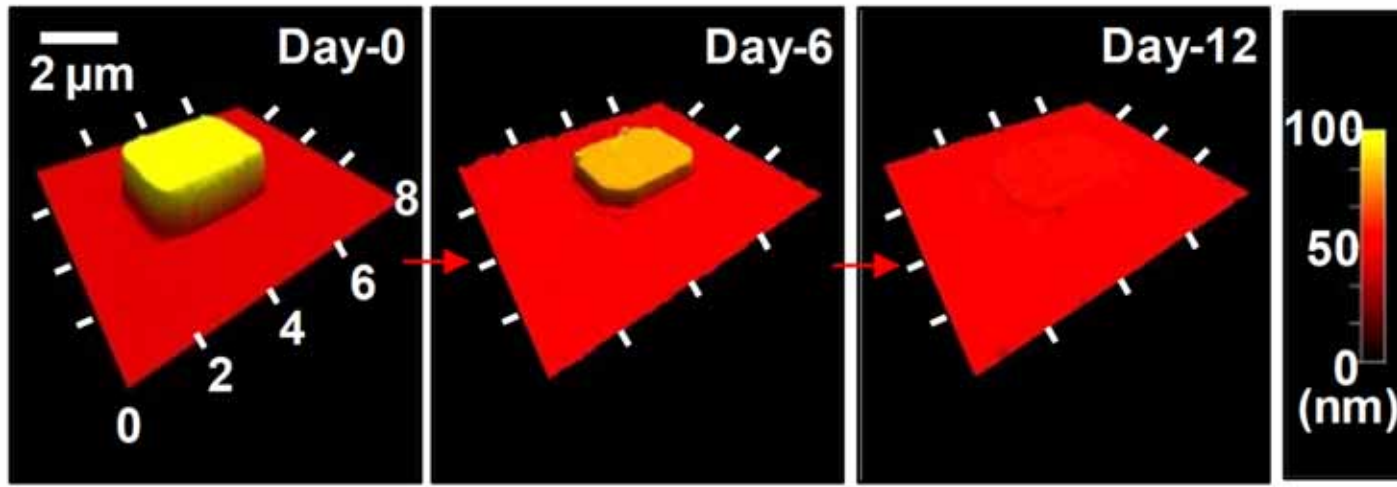
- 1) Zero/Reduced E-Waste Consumer Electronics**
- 2) Temporary Therapeutic / Diagnostic Implants**
- 3) Resorbable Environmental Monitors / Sensors**
- 4) Hardware Secure (non-recoverable) Electronics**
- 5) Hardware Reconfigurable Electronics**

Candidate Semiconductors for Transient Electronics





Dissolution of Si Nanomembranes at Phys. pH, Temp.



Silicon *Can* Dissolve by Hydrolysis

Si for Transient Electronics:

Si thickness: 35 nm (ultrathin, top SOI)

dissolution time: *10 days*

req'd volume of water: 0.4 mL (~ 1 cm²)

Si for Conventional Electronics:

Si thickness: 700 μ m (bulk wafer)

dissolution time: *600 years*

req'd volume of water: 8 L (~ 1 cm²)

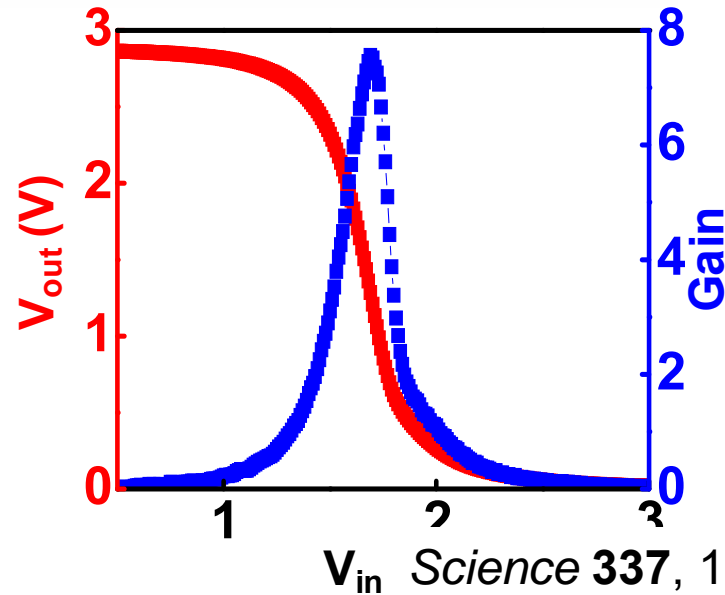
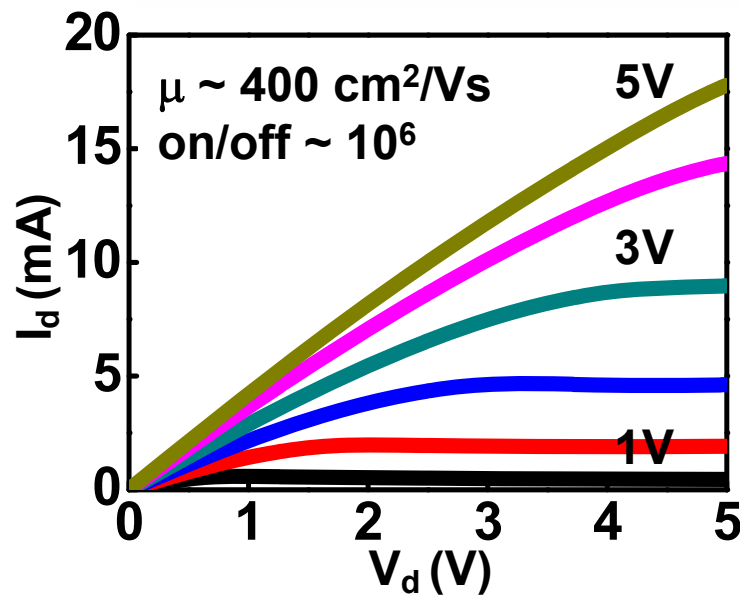
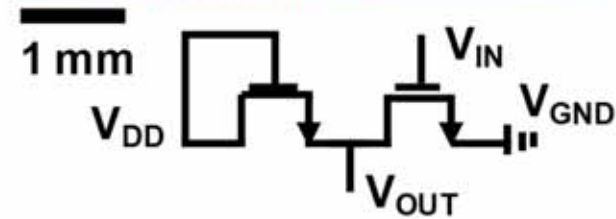
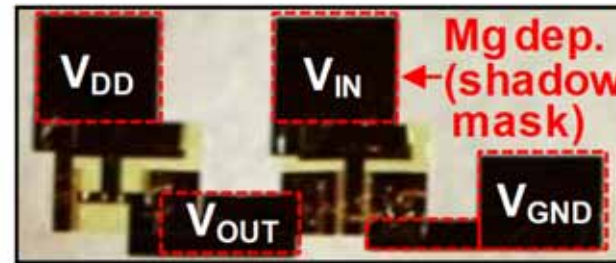
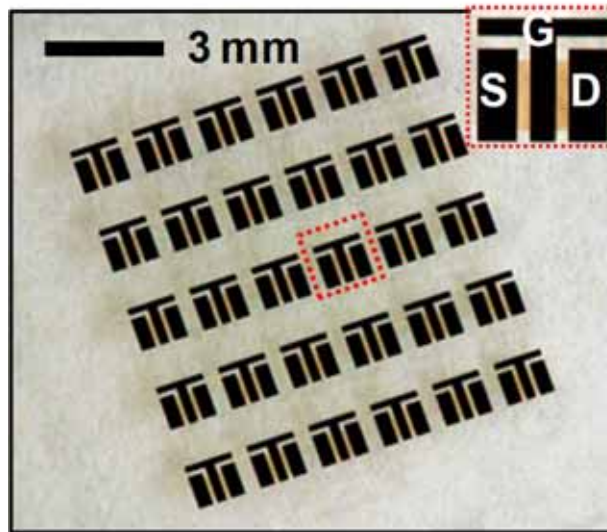
Current Portfolio of Transient Electronic Materials

<u>Semic.</u>	<u>Dielectr.</u>	<u>Interconn.</u>	<u>Substr.</u>
ZnO	SiO _x	Mg	silk
IGZO	SiN _x	Zn	PLGA
poly-Si	MgO	W	PLA
a-Si	SOG	Mo	PCL
np-Si		Fe	POC
Ge		pastes	collagen
SiGe			polyanhydride
			metal foils

Adv. Mater. **26**, 7637 (2014).
Adv. Mater. **26**, 7371 (2014).
Adv. Mater. **26**, 3905 (2014).
ACS Nano **8**, 5843 (2014).
APL **105**, 013506 (2014)
Adv. Func. Mater. **24**, 4427 (2014).

Adv. Health. Mater. **3**, 515 (2014).
Small **9**, 3398 (2013).
Adv. Mater. **26**, 3905 (2014).
Adv. Func. Mater. **24**, 645 (2014).
Adv. Func. Mater. **23**, 4087 (2013).
Adv. Mater. **25**, 3526 (2013).

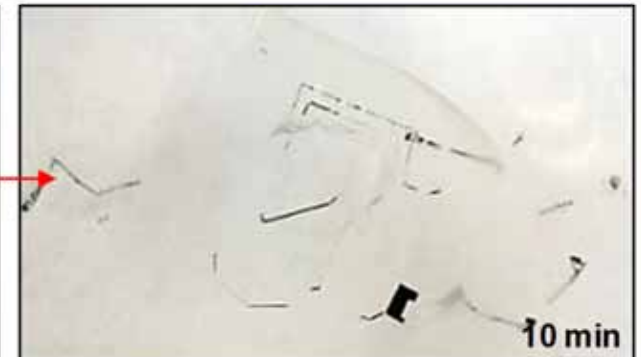
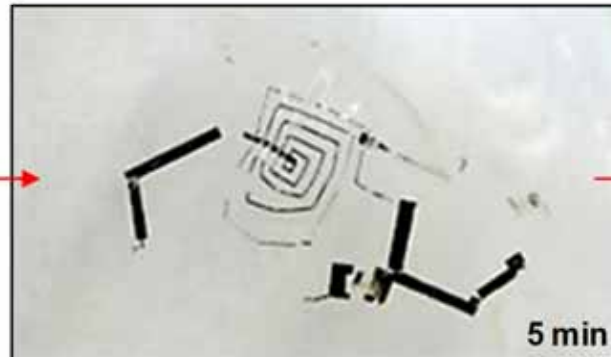
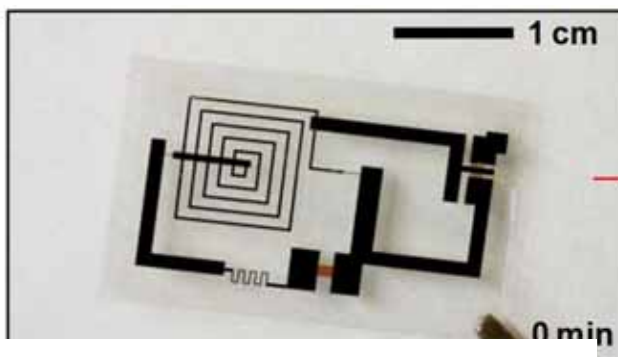
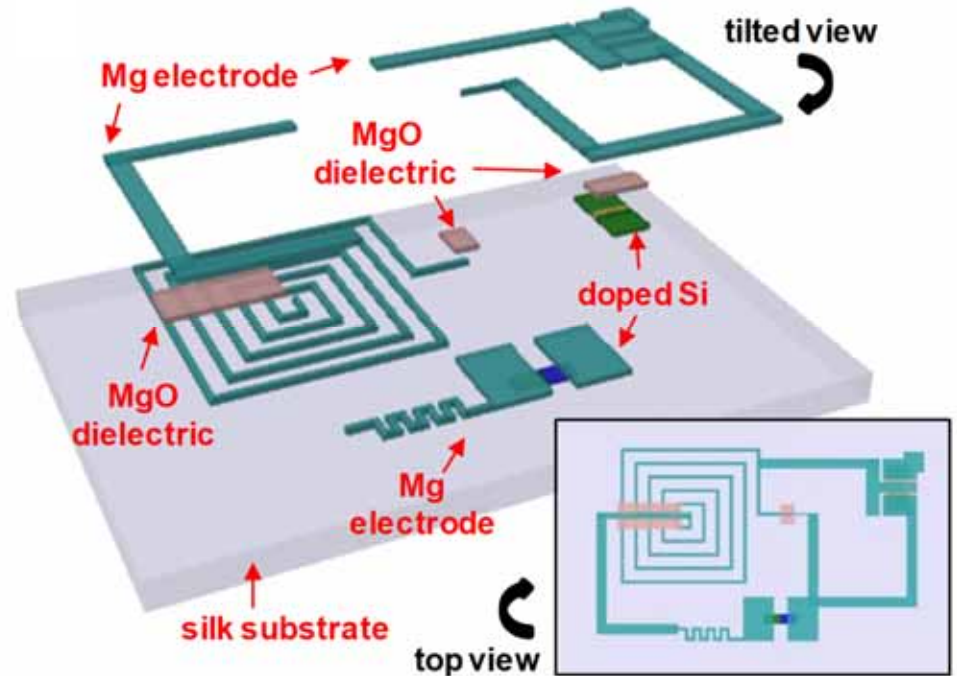
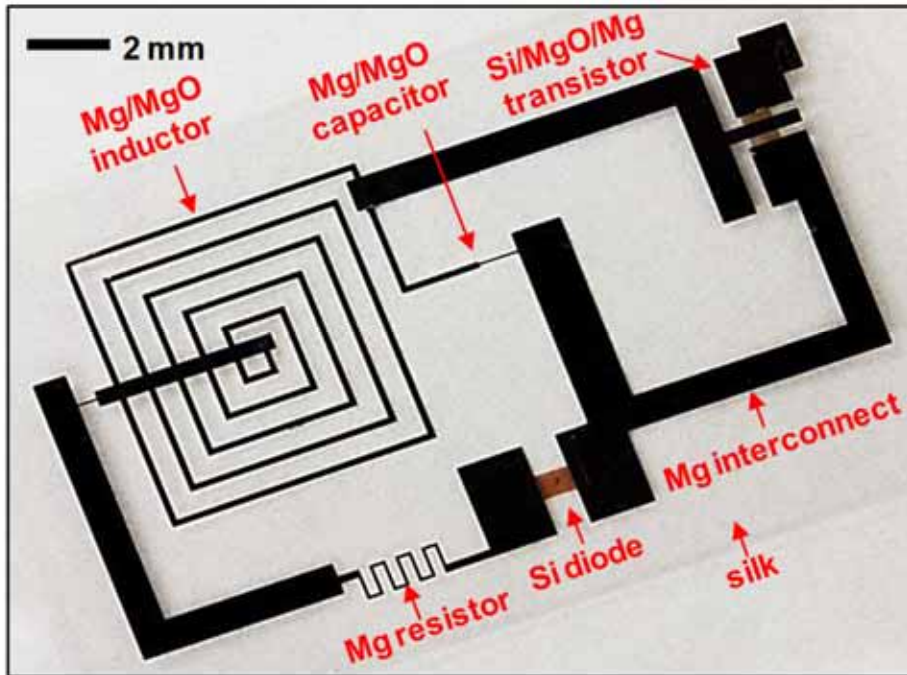
Transient Si MOSFETS and Logic Gates



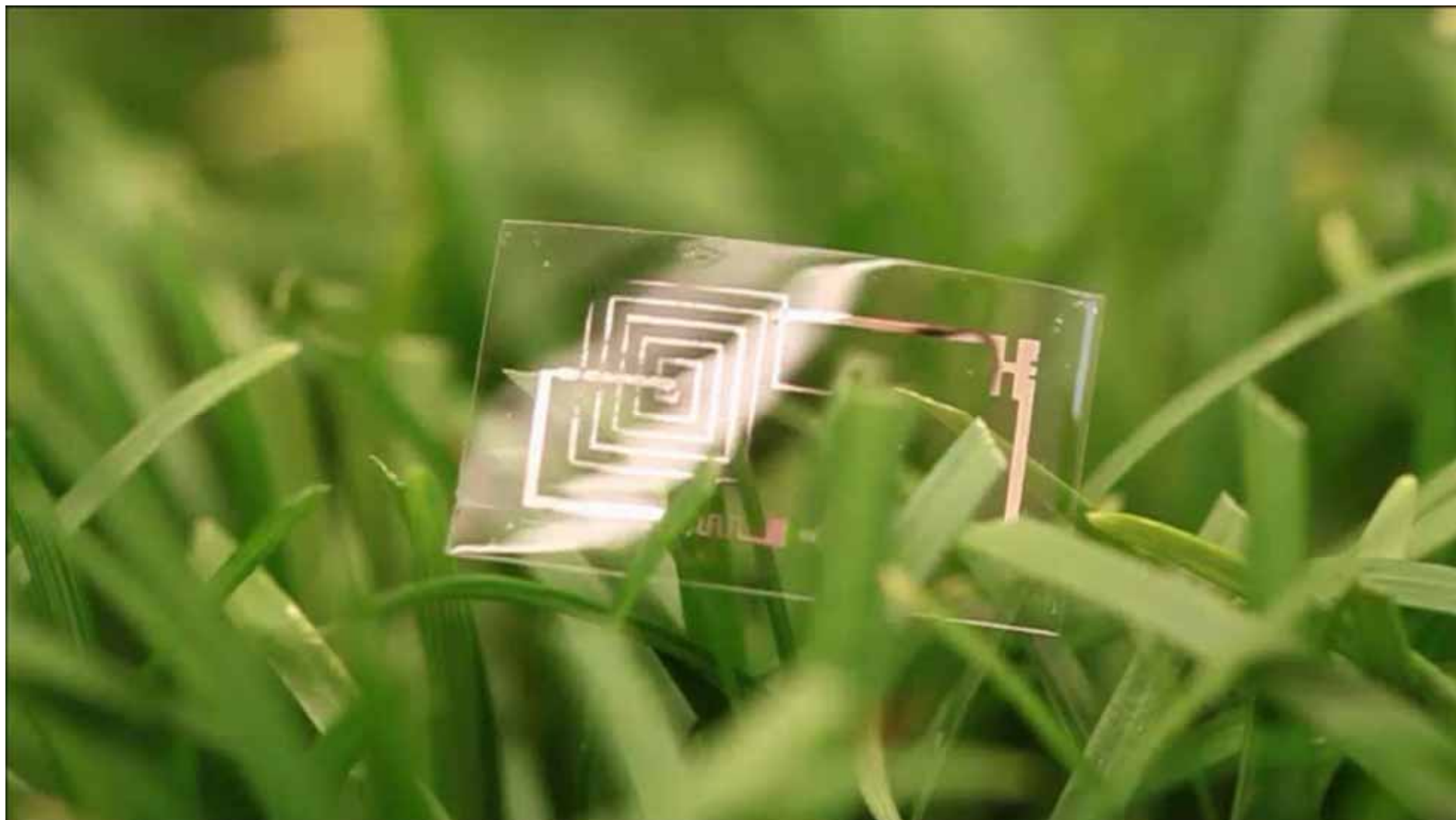
V_{in} Science 337, 1640 (2012).

Transient Electronics – Test Platform

Si, SiO₂, Mg, MgO and silk



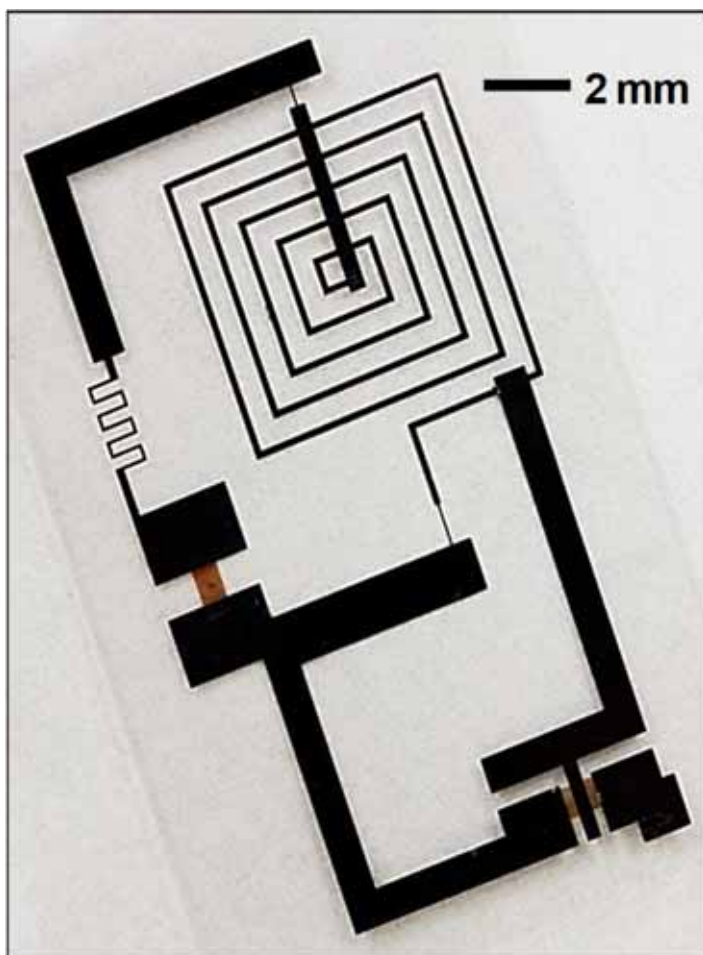
Science 337, 1640 (2012).



Science **337**, 1640 (2012).

Perspective on Elemental Content

Transient Electronics



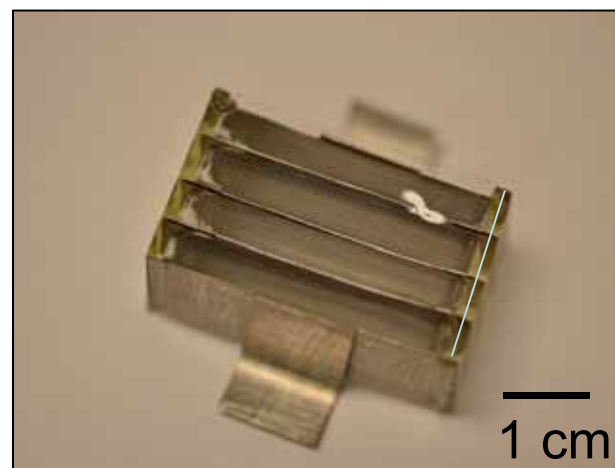
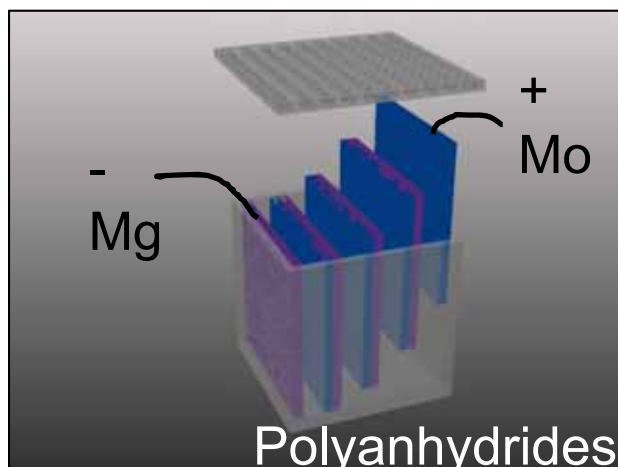
Mg ~100 μ g, Si ~ 3 μ g

Rec. Daily Intake



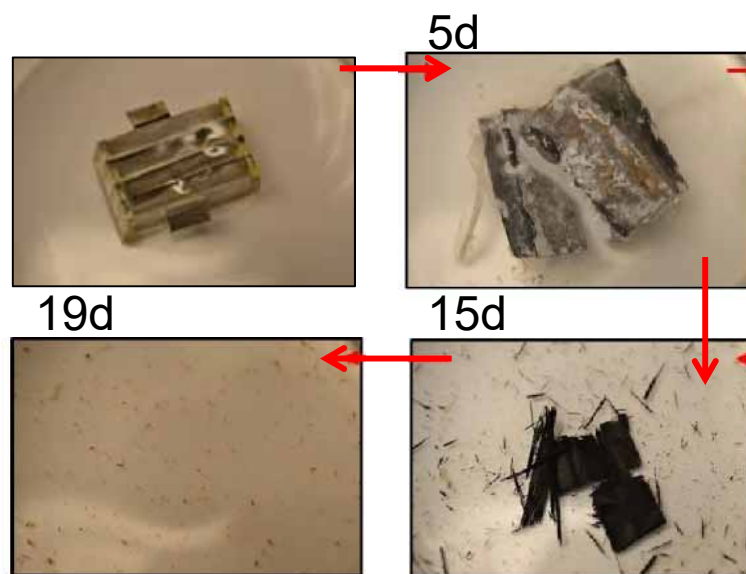
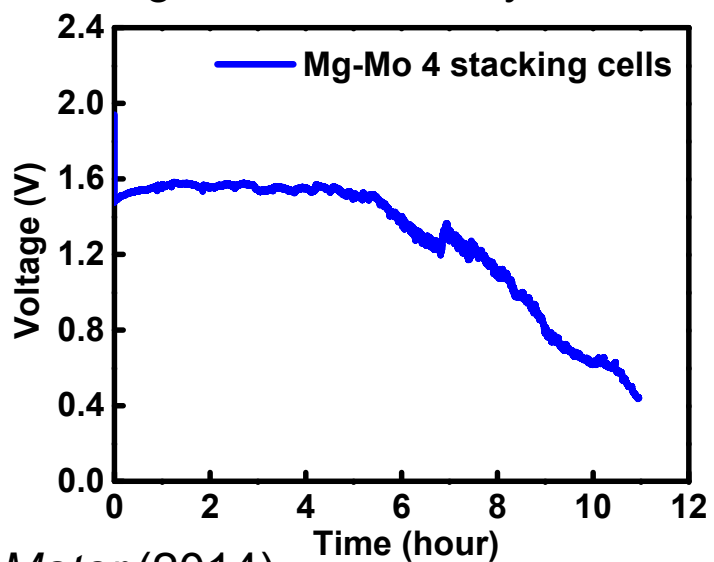
Mg ~300 mg, Si ~10 mg

Transient, Water-Activated Mg Primary Battery

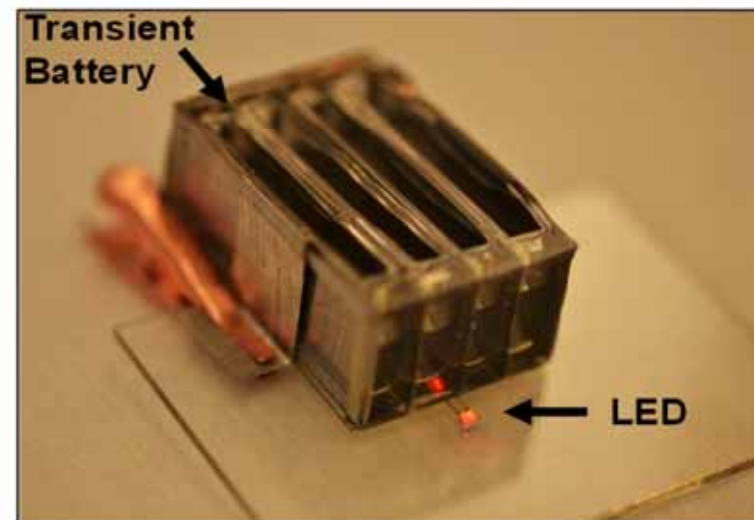
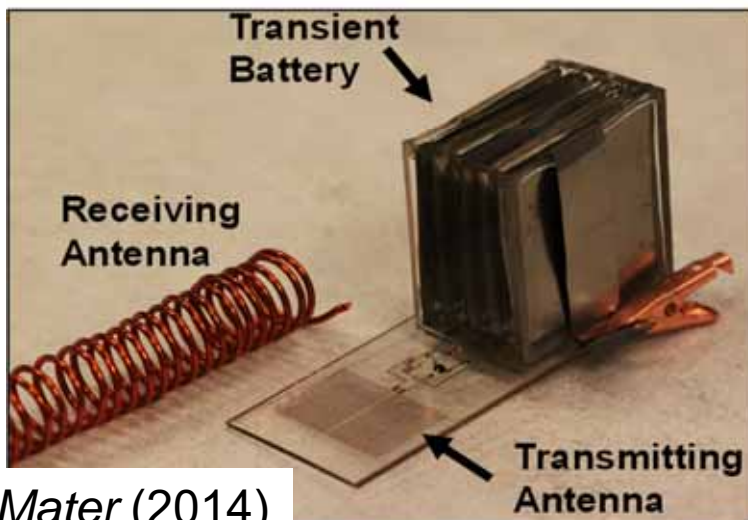
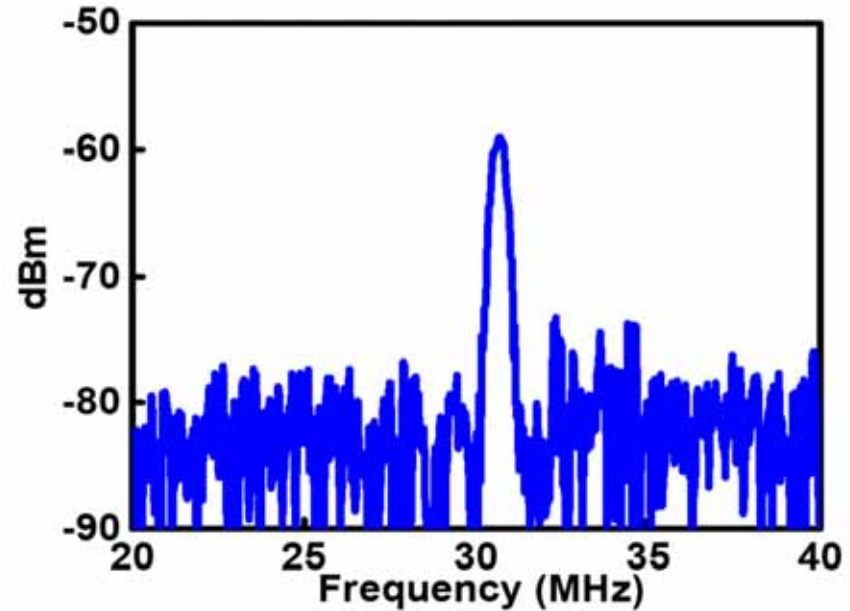
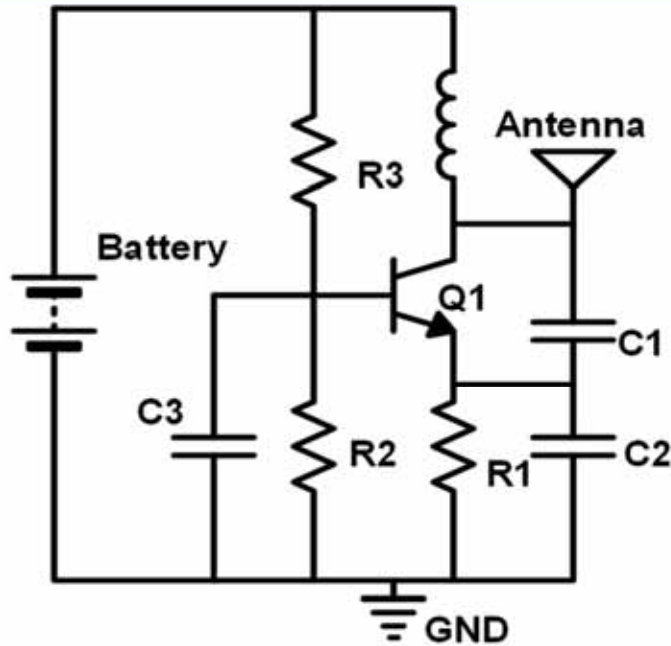


Dissolution in Water

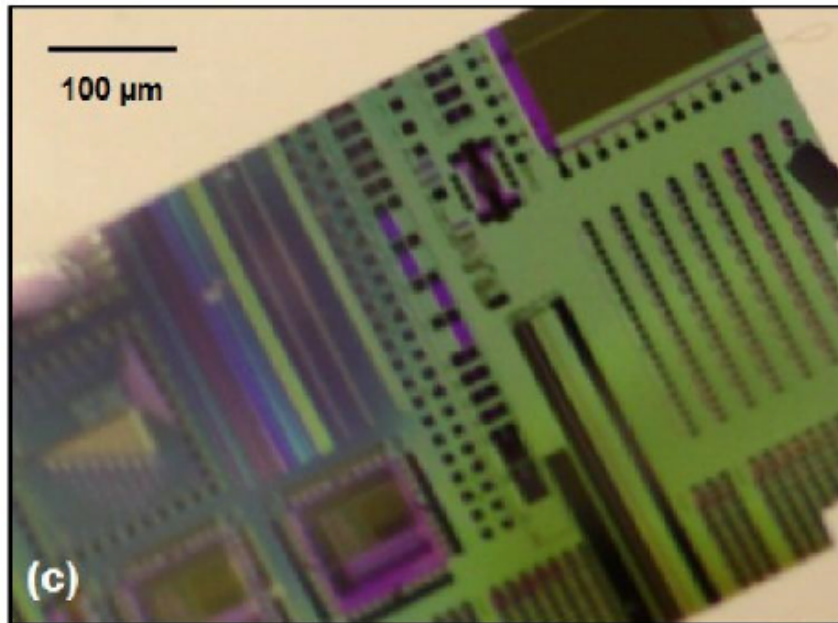
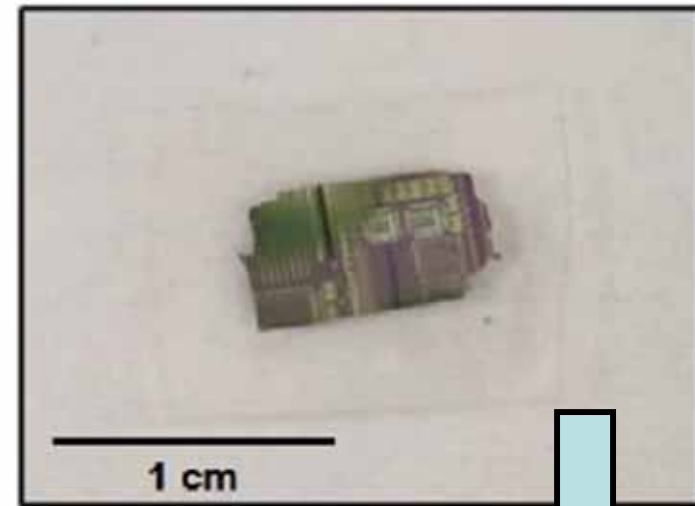
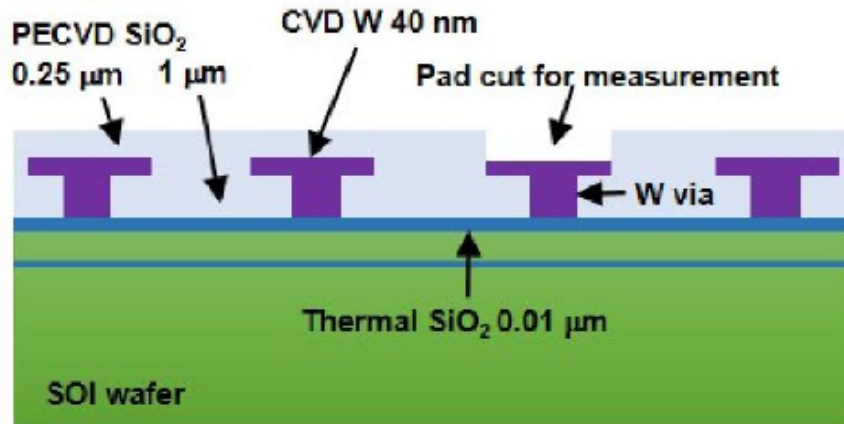
Discharge current density: 0.1 mA/cm²



Transient Battery Power for Radios, LEDs

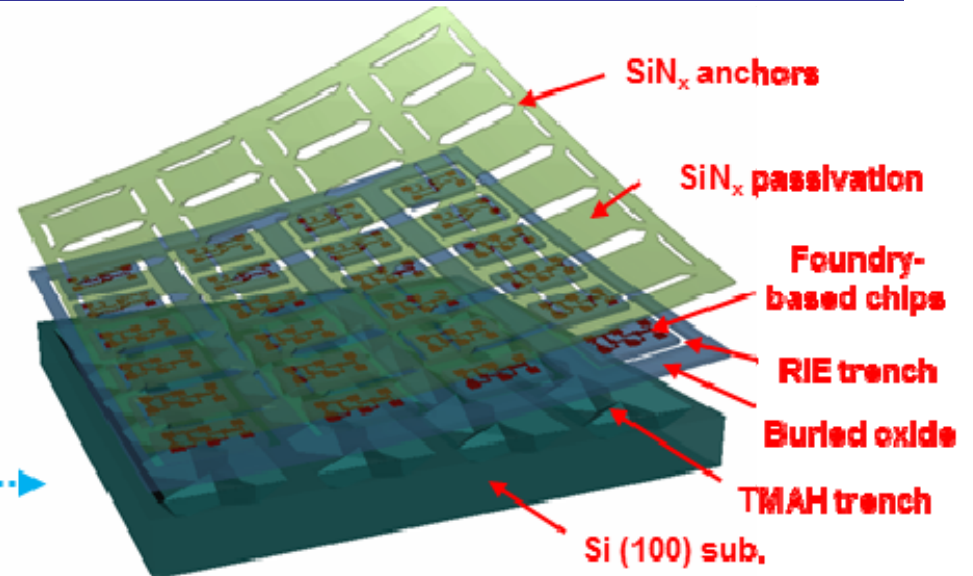
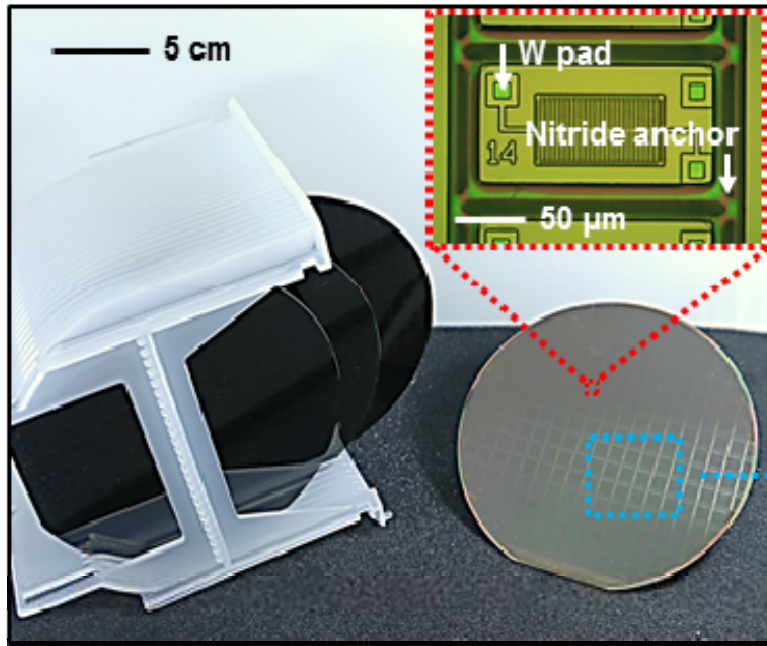


Transient Electronics from a 90 nm CMOS Foundry



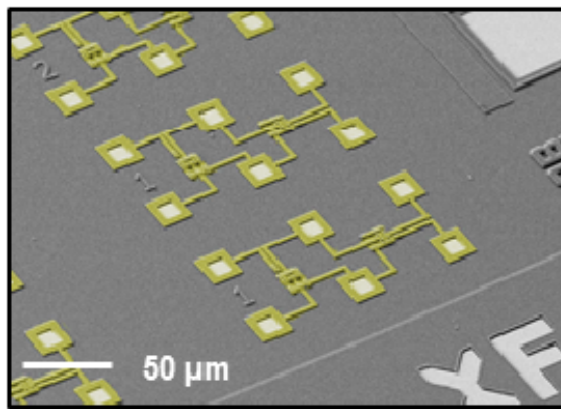
Appl. Phys. Lett **106**, 014105 (2015).

Transient SOI CMOS from a Commercial Foundry (X-Fab Intl)

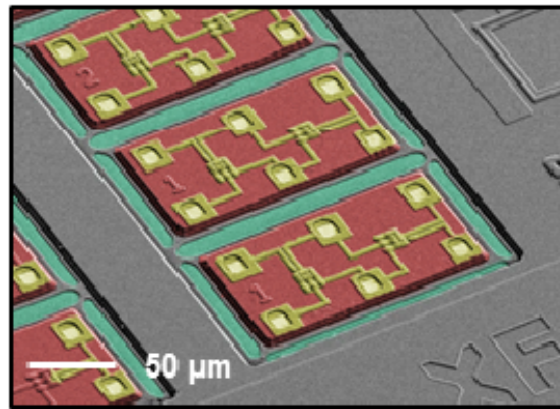


Foundry-based devices on Si (100) wafer after TMAH etching

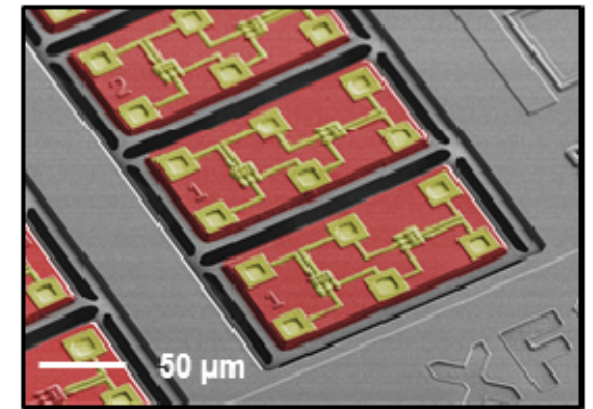
PNAS 114, E5522 (2017).



Device array on Si (100) wafer



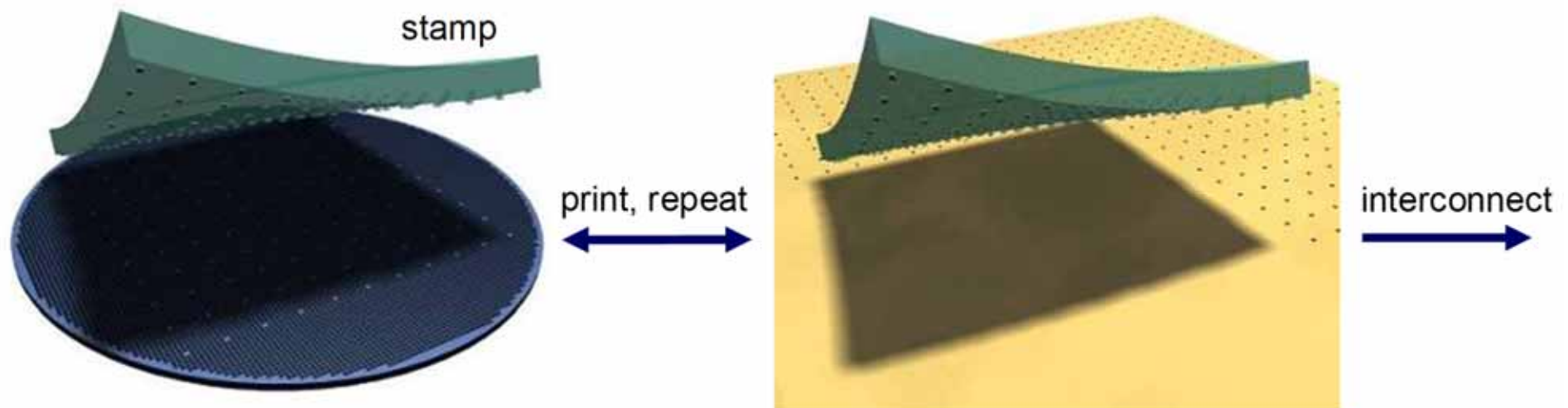
Nitride passivation & trench etch



TMAH undercut

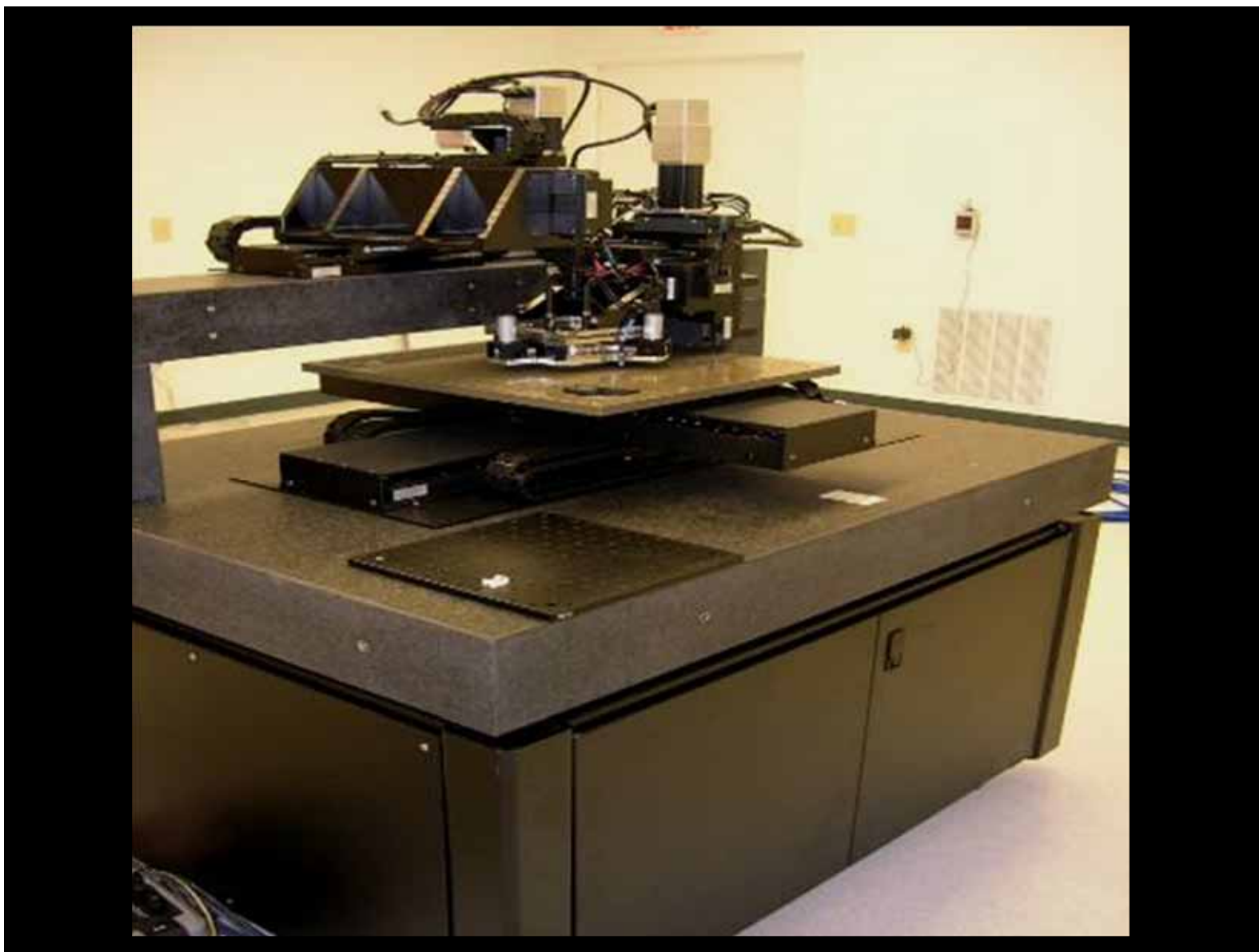
Rapid, Precise Materials/Device Assembly via Printing

- 1) Form undercut microdevices, anchored at endpoints
- 2) Transfer them to a target substrate by printing
- 3) Interconnect to form systems

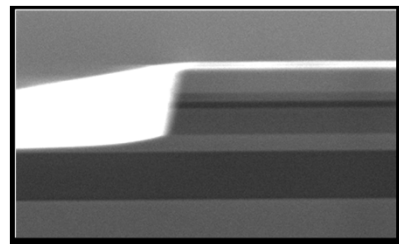


Nature Mater **5**, 33 (2006). *PNAS* **107**, 17095 (2010).

Semiconductor Device 'Printer'



Processing and Printing of AlInGaP μ -LEDs



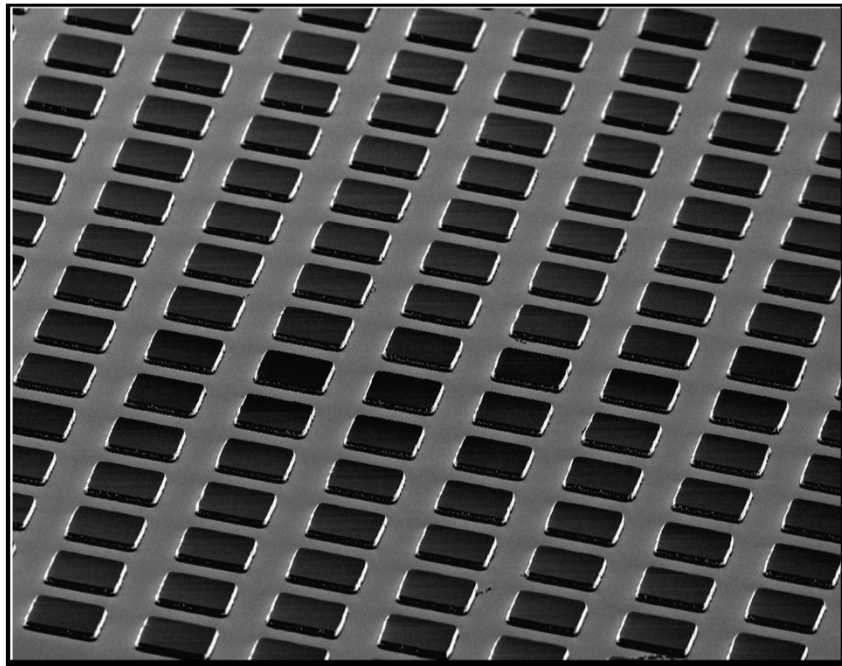
device stack
AlAs layer
GaAs wafer

2 μ m

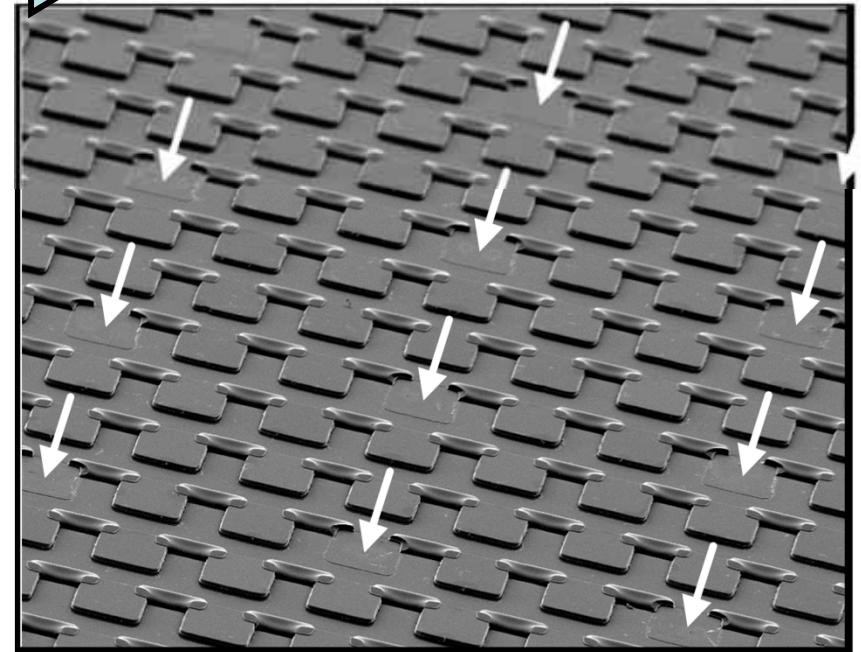
anchor with PR;
undercut etch AlAs



10 μ m



50 μ m

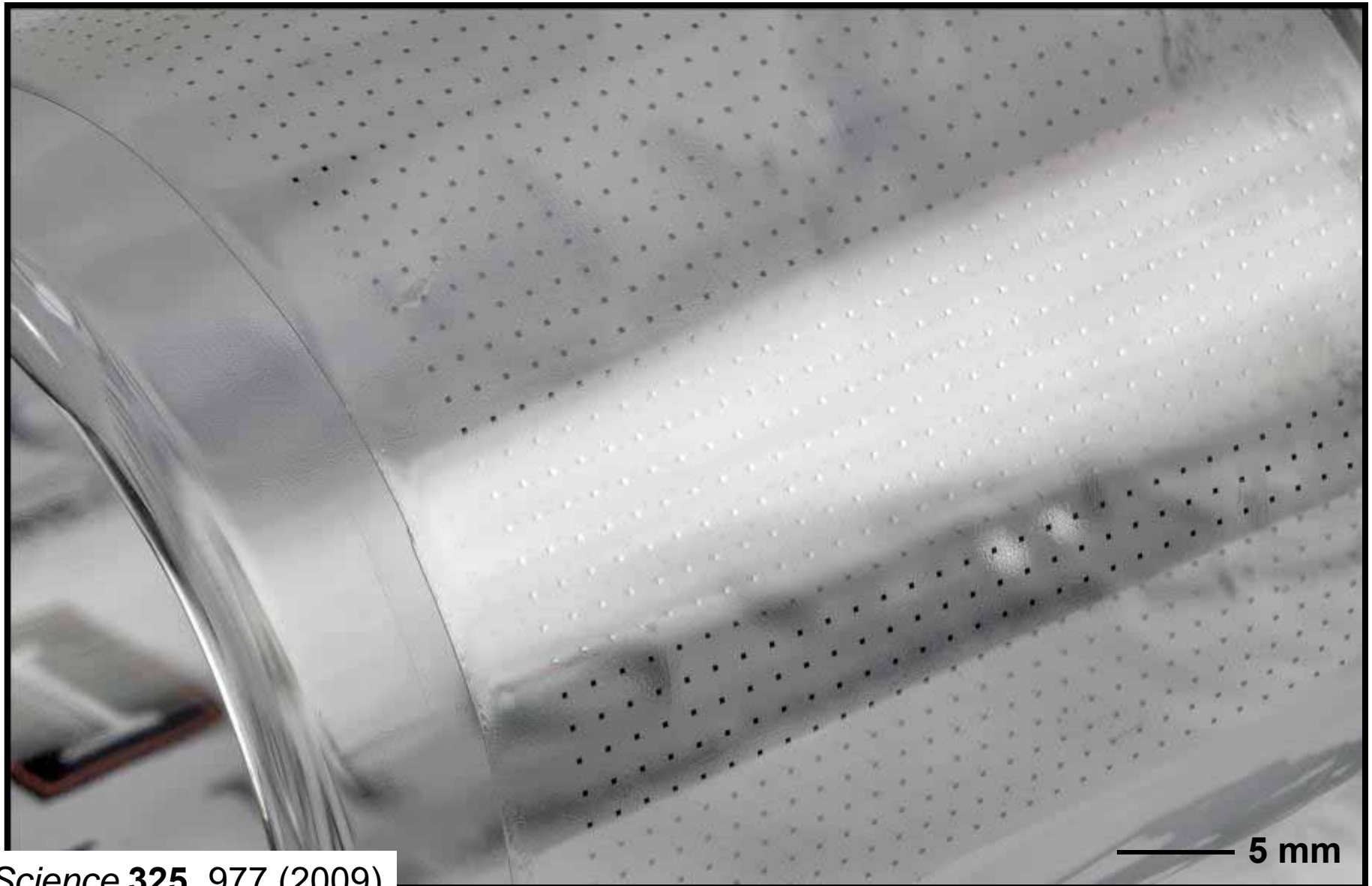


50 μ m

Science 325, 977-981 (2009).

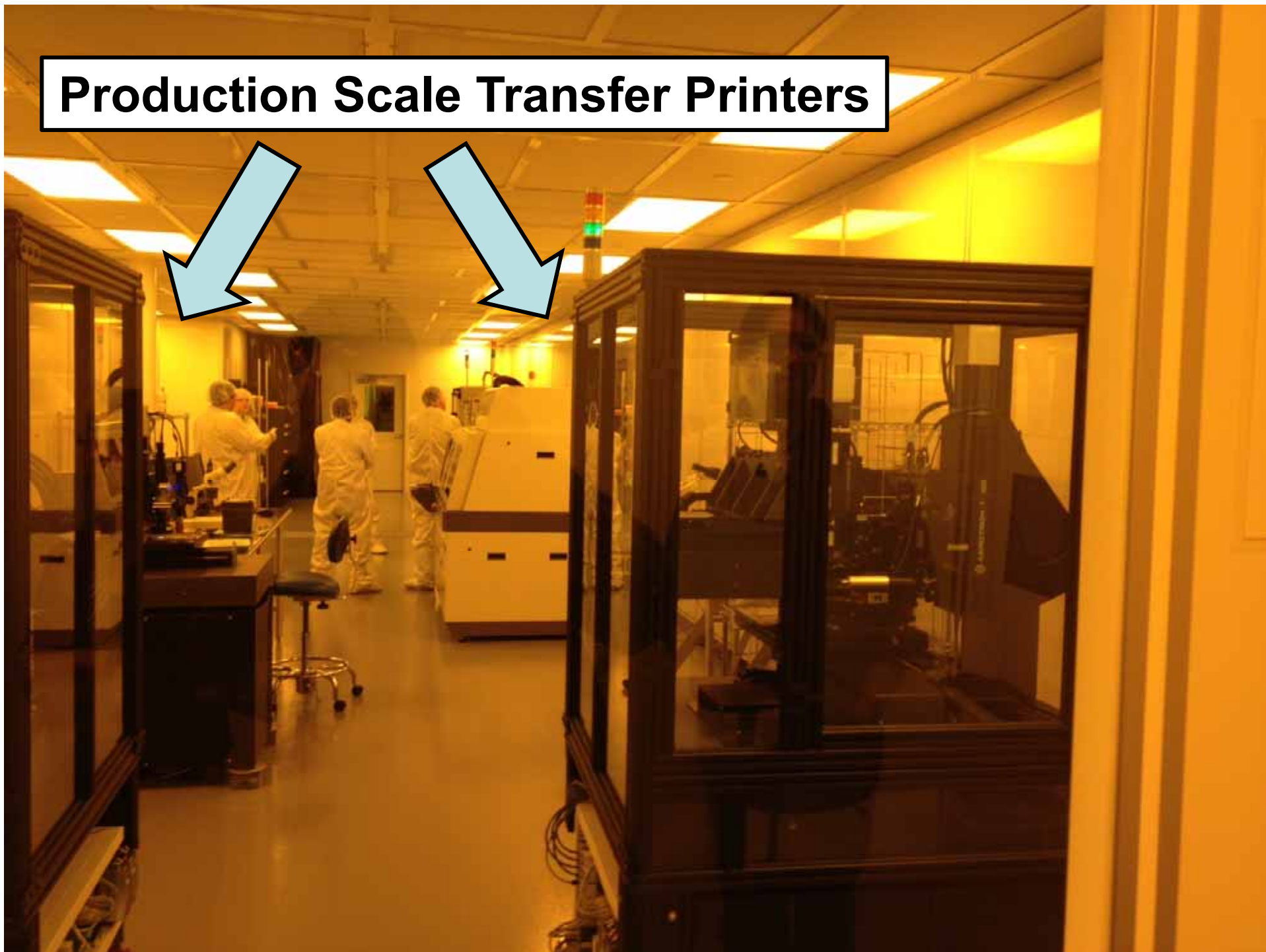
unpublished

AllnGaP μ -ILEDs Printed Onto Plastic (1600; 100% yield)

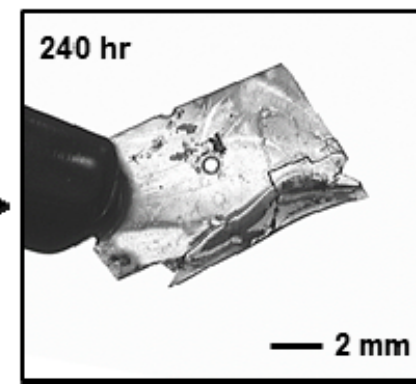
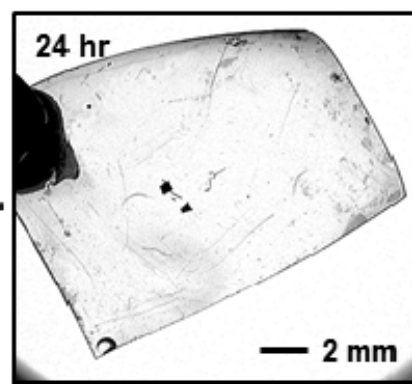
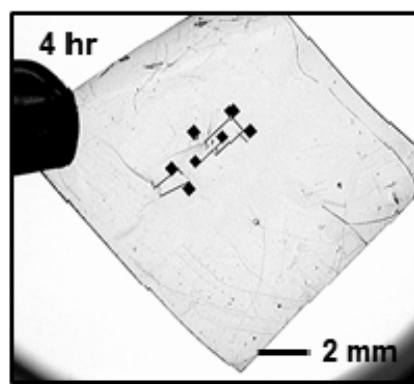
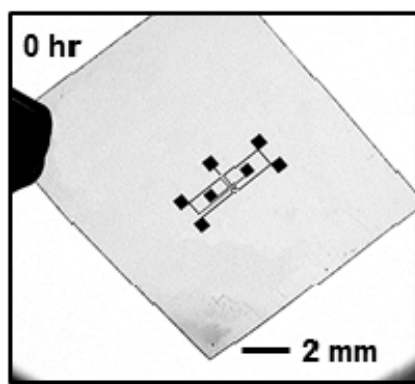
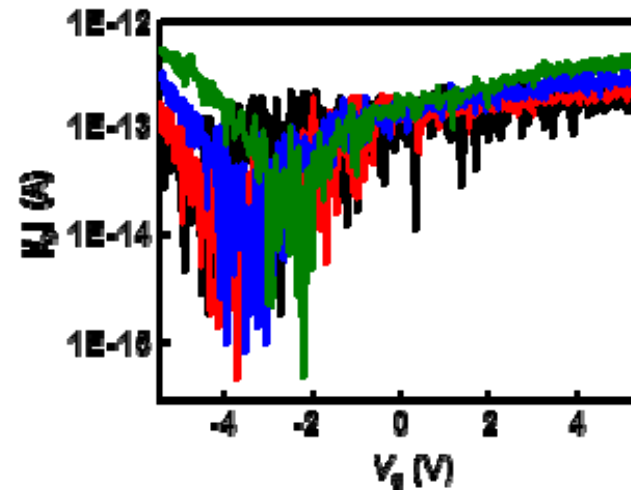
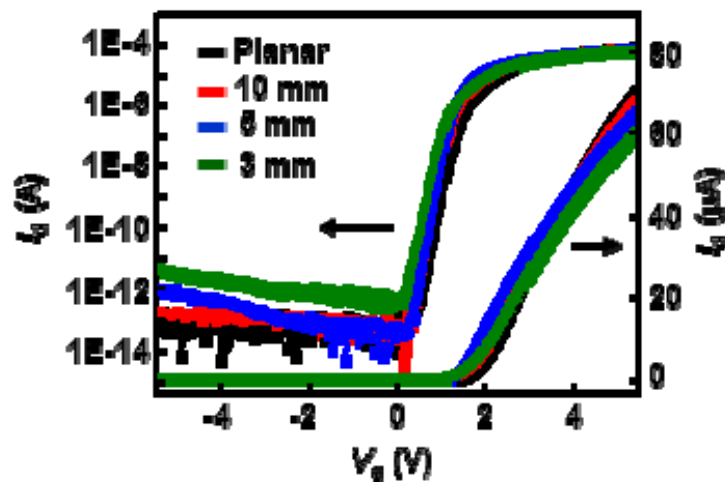
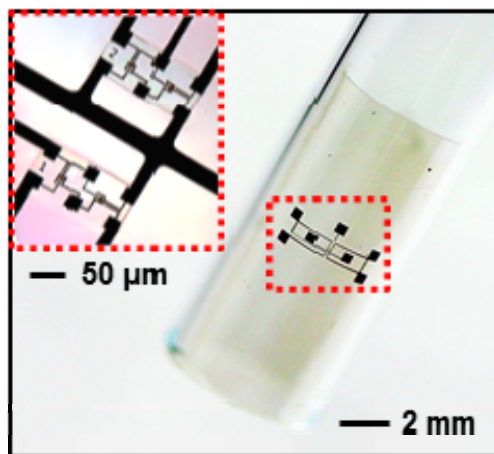


Science **325**, 977 (2009)

Production Scale Transfer Printers



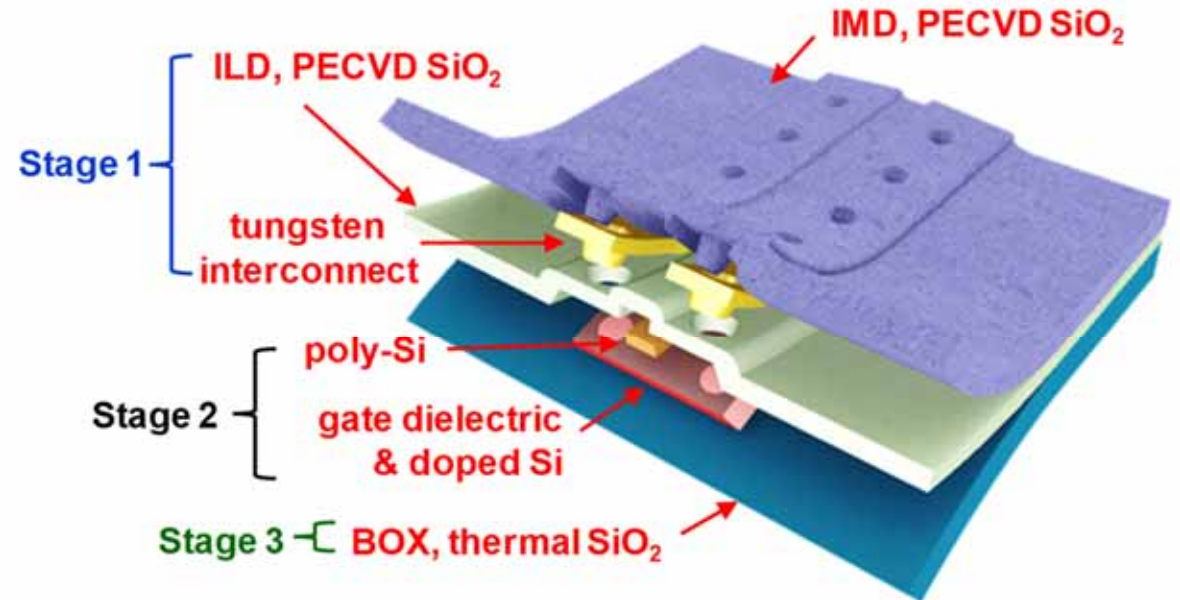
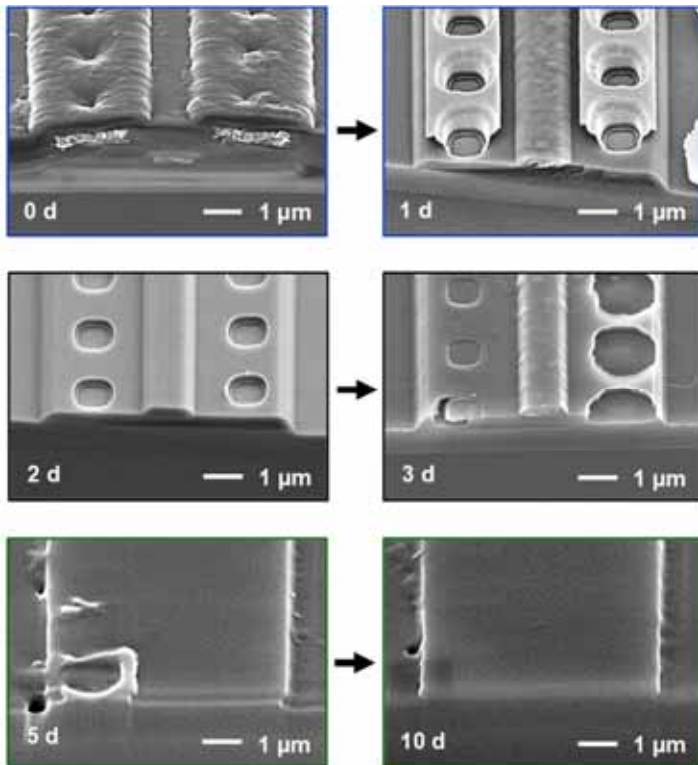
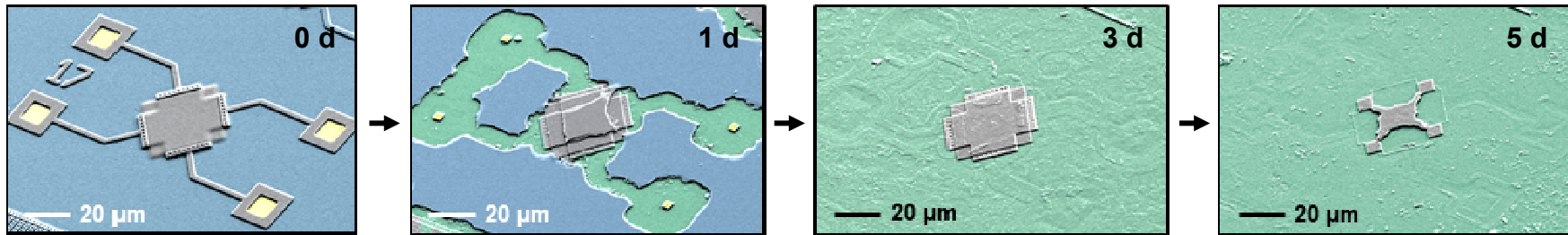
Transient SOI Electronics on Flexible PLGA Substrates



PNAS 114, E5522 (2017).

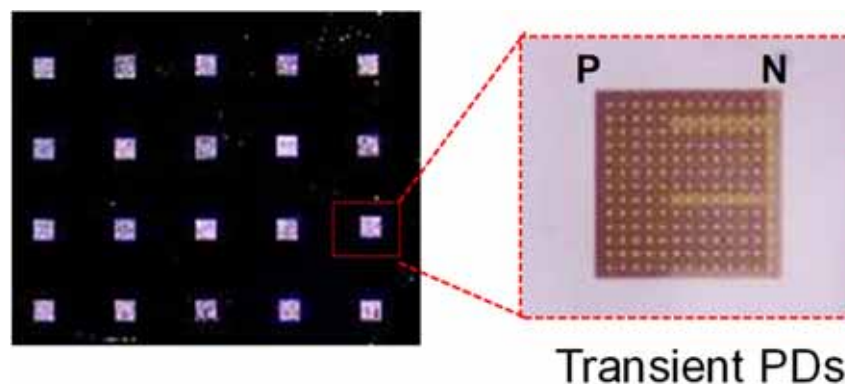
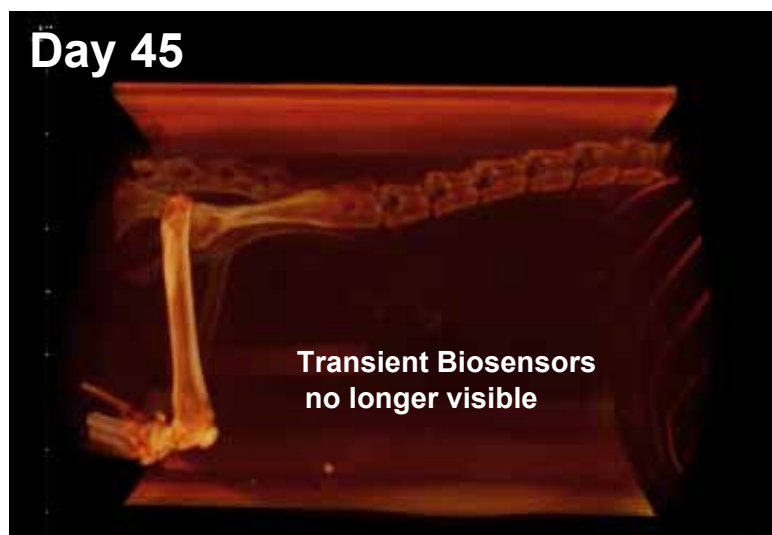
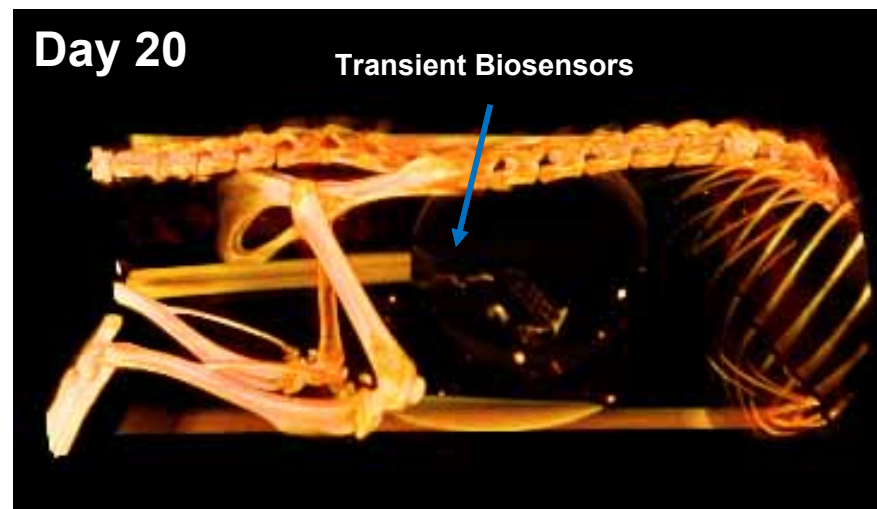
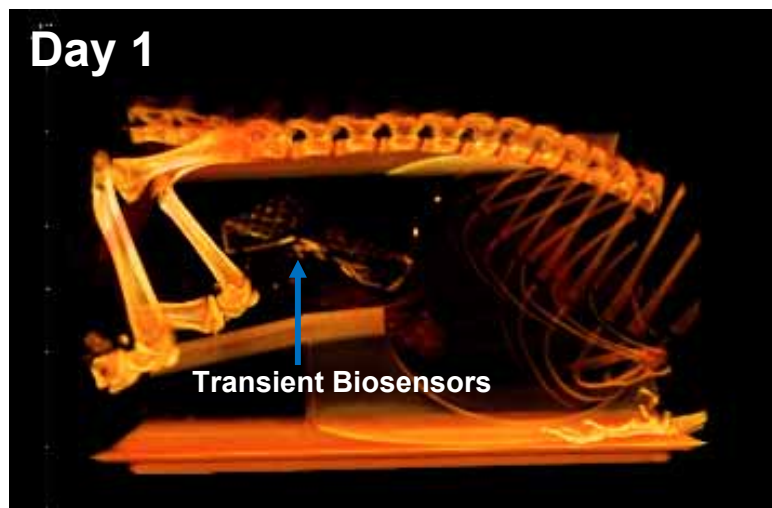
Dissolution / Disintegration of Transient CMOS

Complete dissolution ~20 days: everything except BOX is eliminated in 6 days.



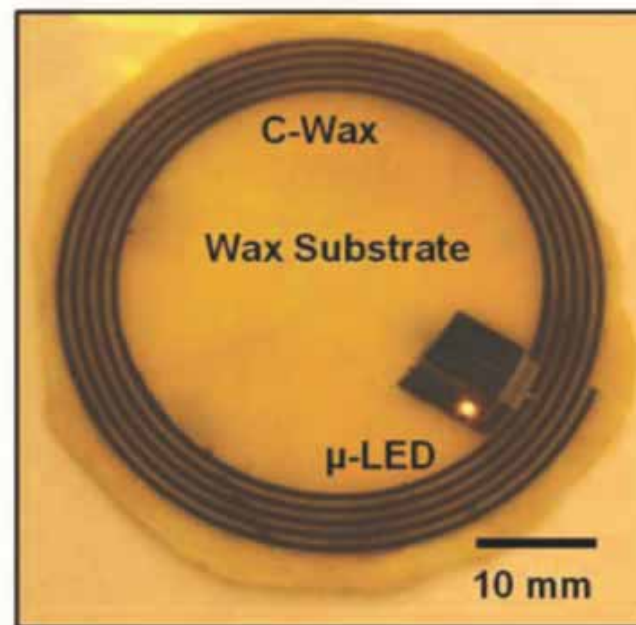
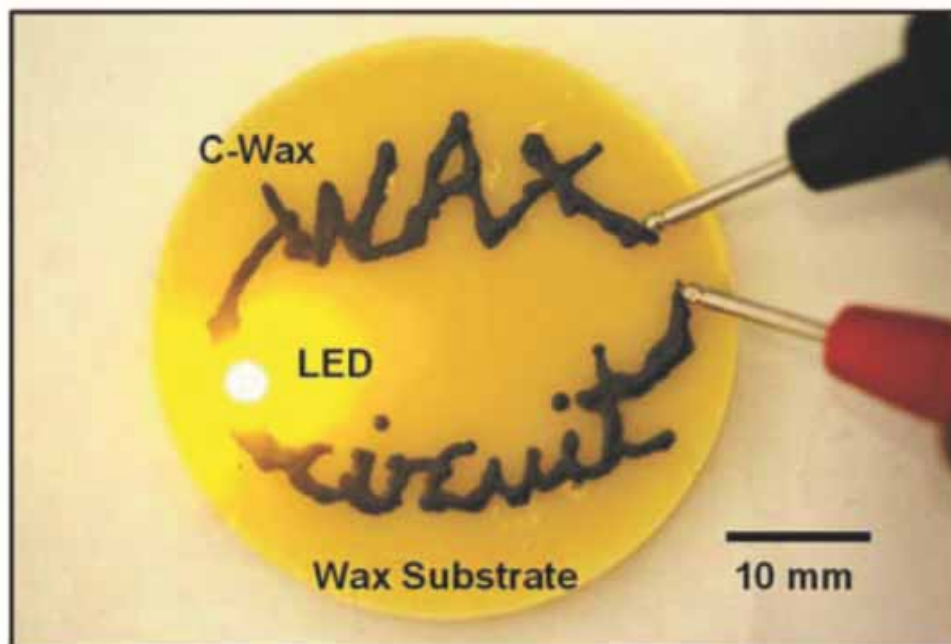
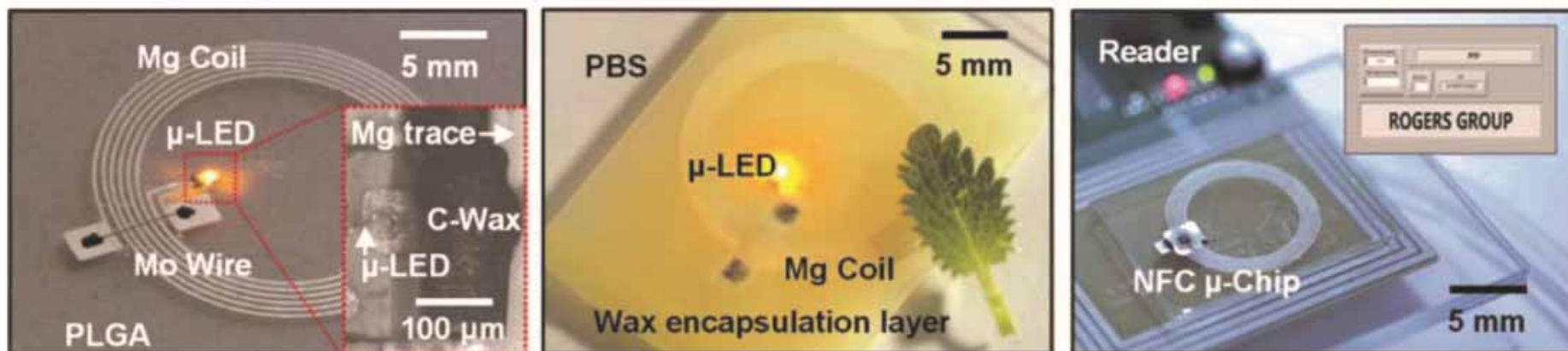
Adv. Mater. **11**, 1704955 (2018).

In Vivo Bioresorption of an Array of Transient Devices



- Full dissolution in 45 days.
- No abnormalities or adverse effects.

Printable Transient Conductors: W in Wax for RFID Tags



Intracranial Monitors for TBI

Current

Non-degradable → Secondary surgery
Wired operation → Restricted movement
External interface → Infection / hemorrhage

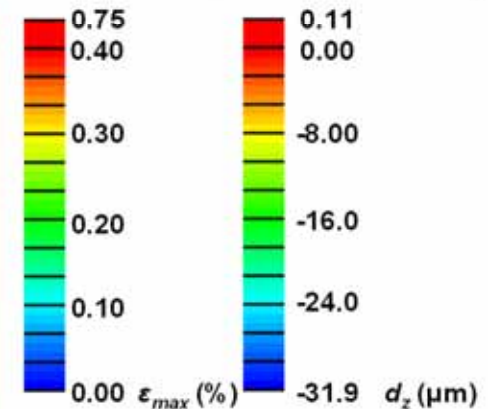
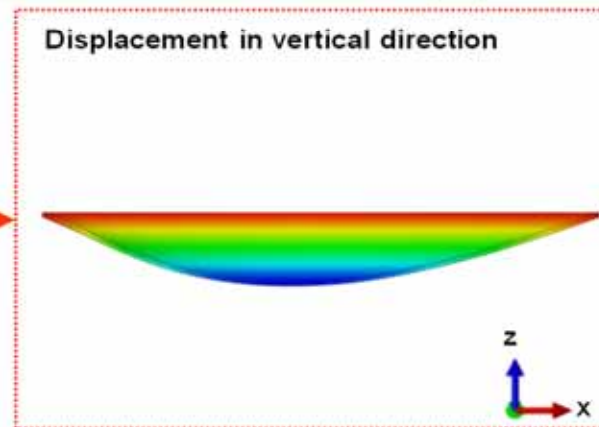
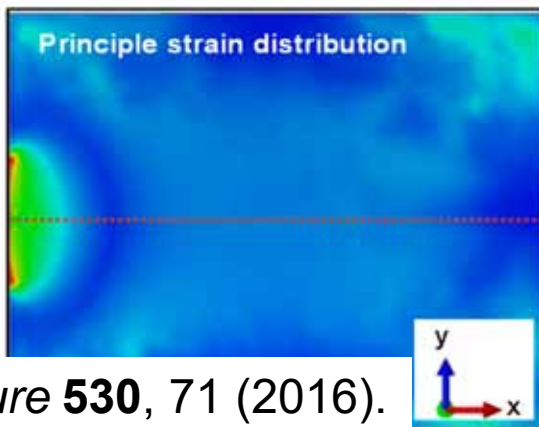
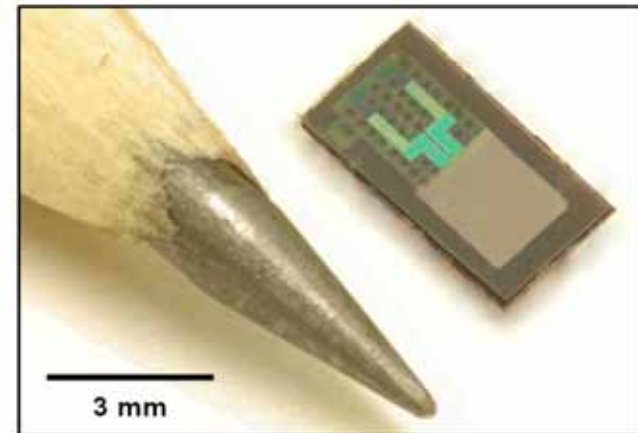
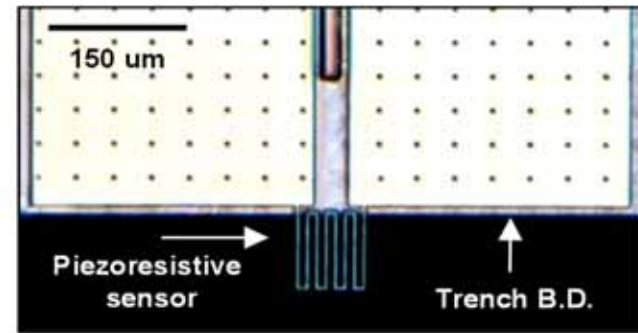
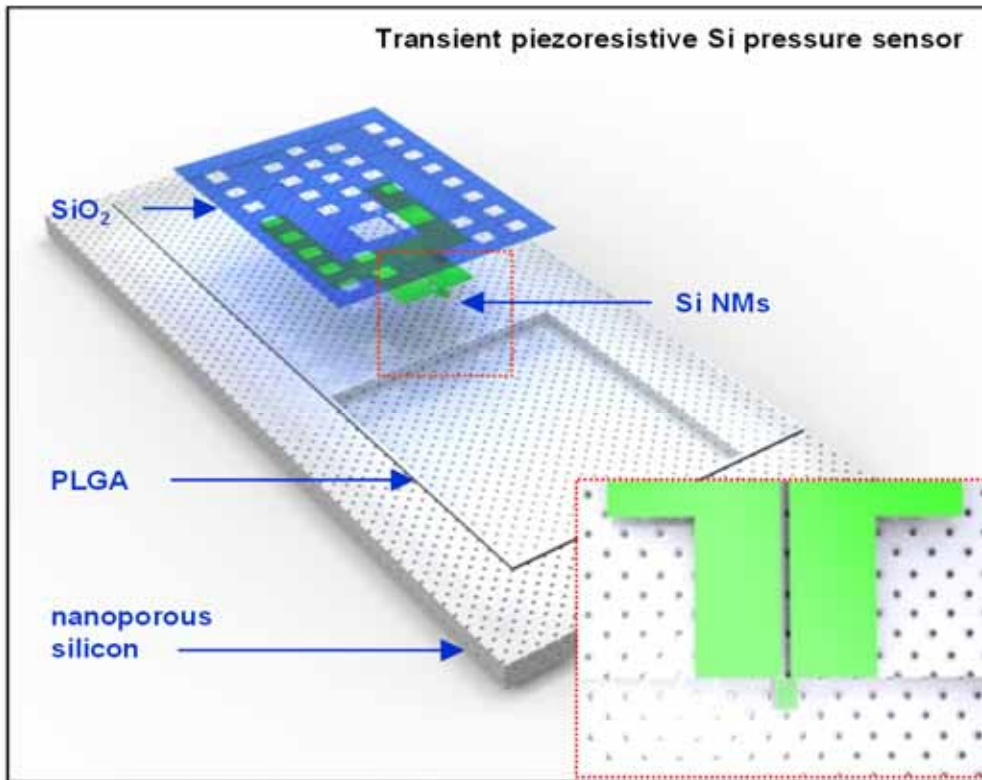


Future

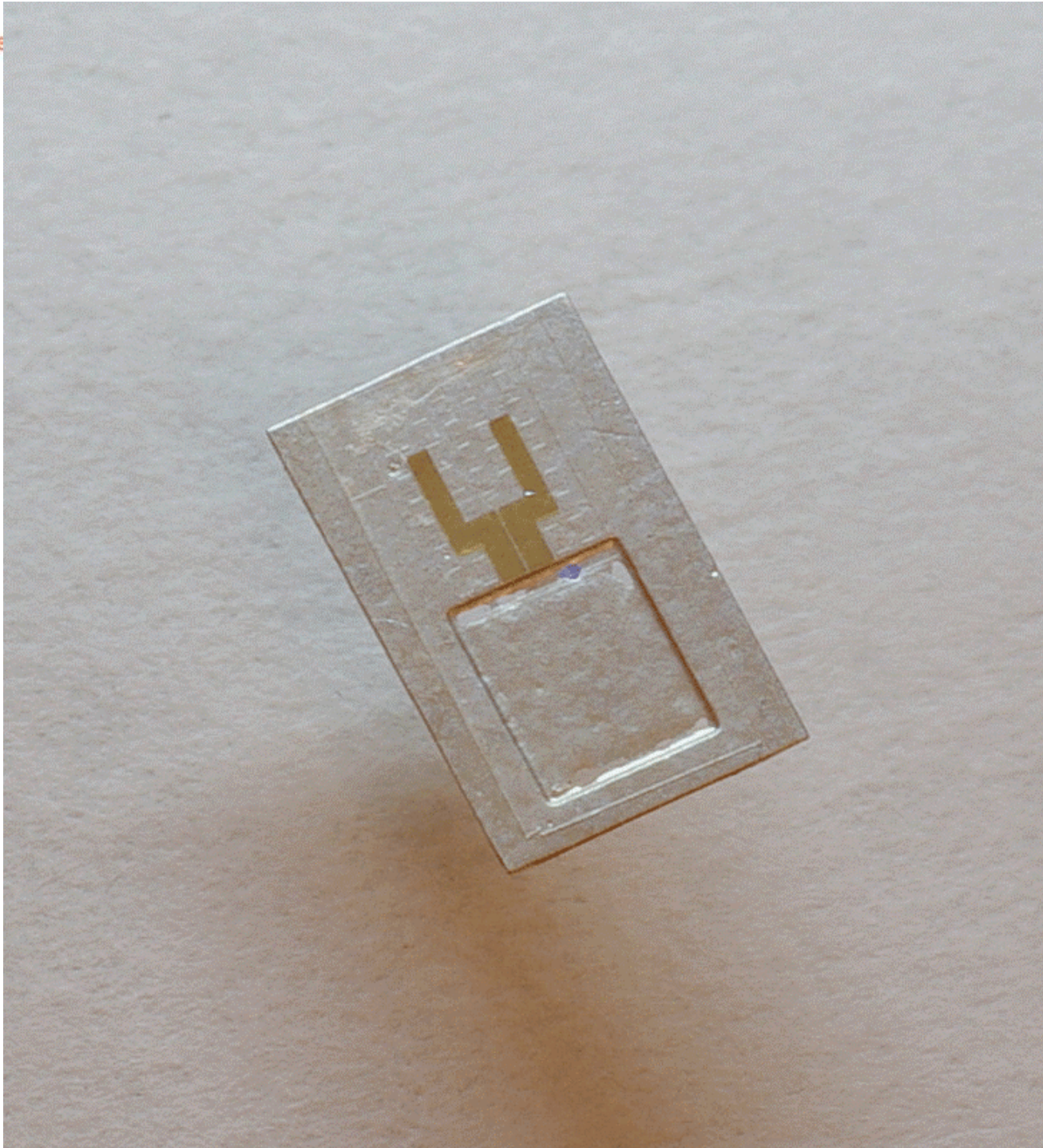
Bioresorbable → Eliminate extraction
Wireless operation → Free movement
Fully sutured → Safe, minimal risk



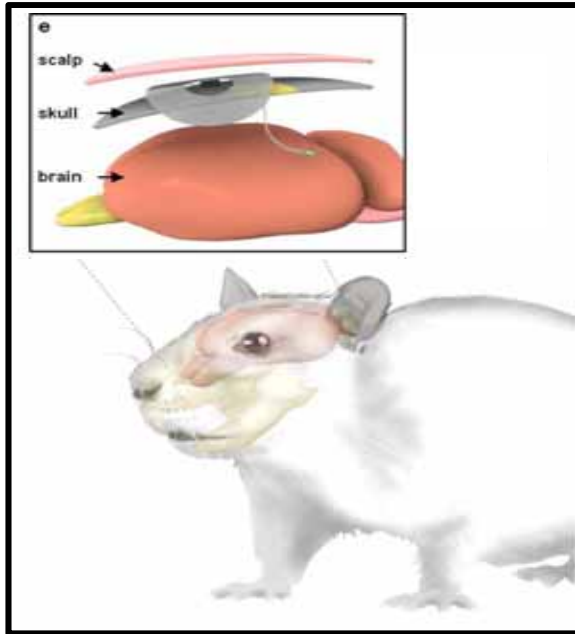
Bioresorbable Intracranial Pressure Sensors for TBI



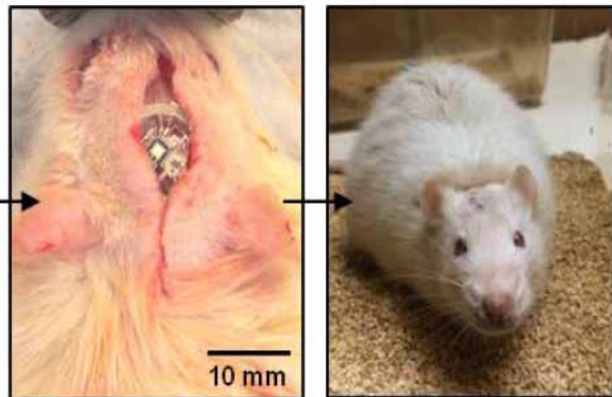
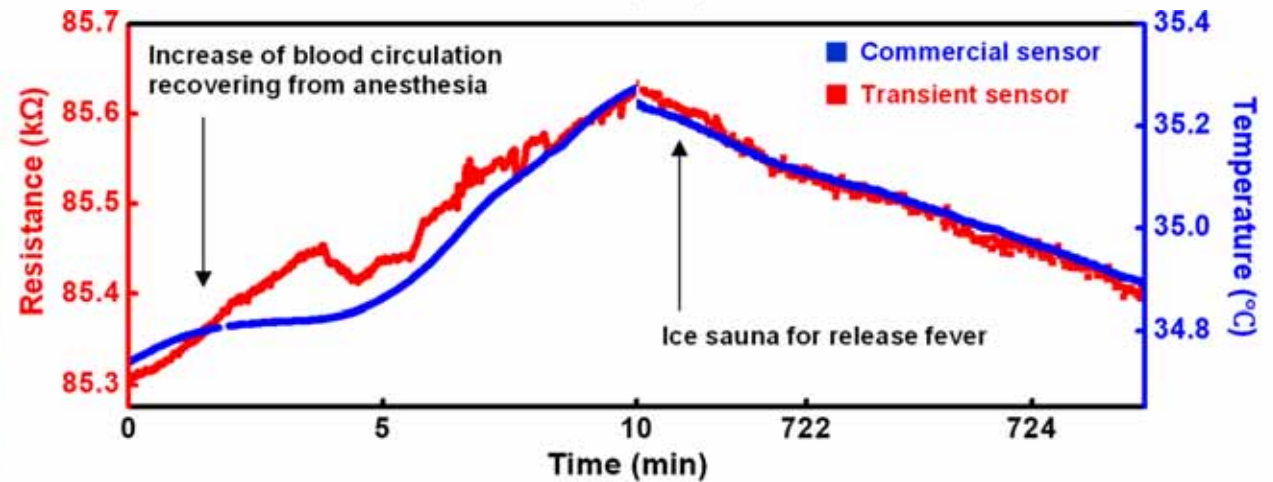
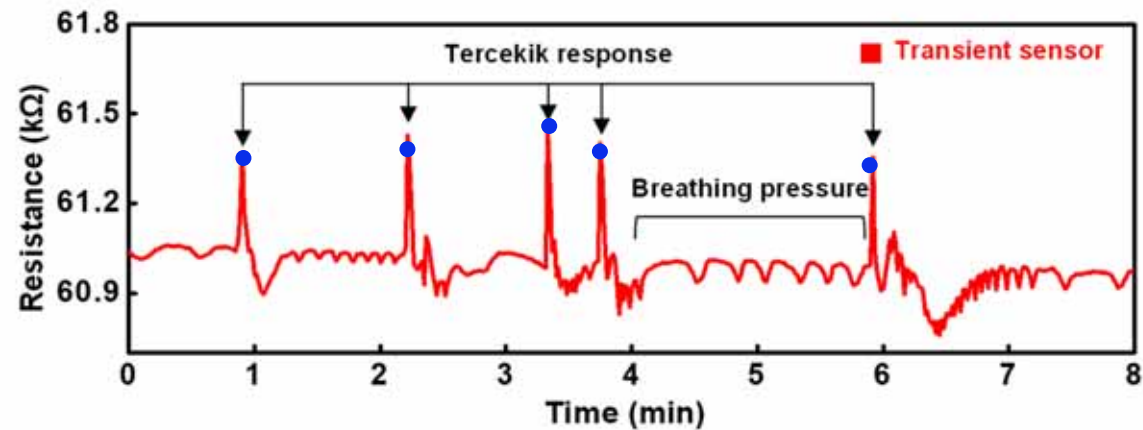
Nature **530**, 71 (2016).



In-vivo Wireless Monitoring – Pressure and Temperature



In-vivo Results Using A Rat Model



Electronic Medicines – Active Project Areas

Programmable Drug Release -- therapeutic

Pacemakers – recovery

Intracranial monitors -- recovery

Nerve Stimulators – accelerated healing

Bone Stimulators – accelerated healing

Thermal Therapy – anti-bacterial

Senior Collaborators

Engineering Science

Prof. Y. Huang (NU) – mechanics

Prof. P. Ferreira (UIUC) – manuf.

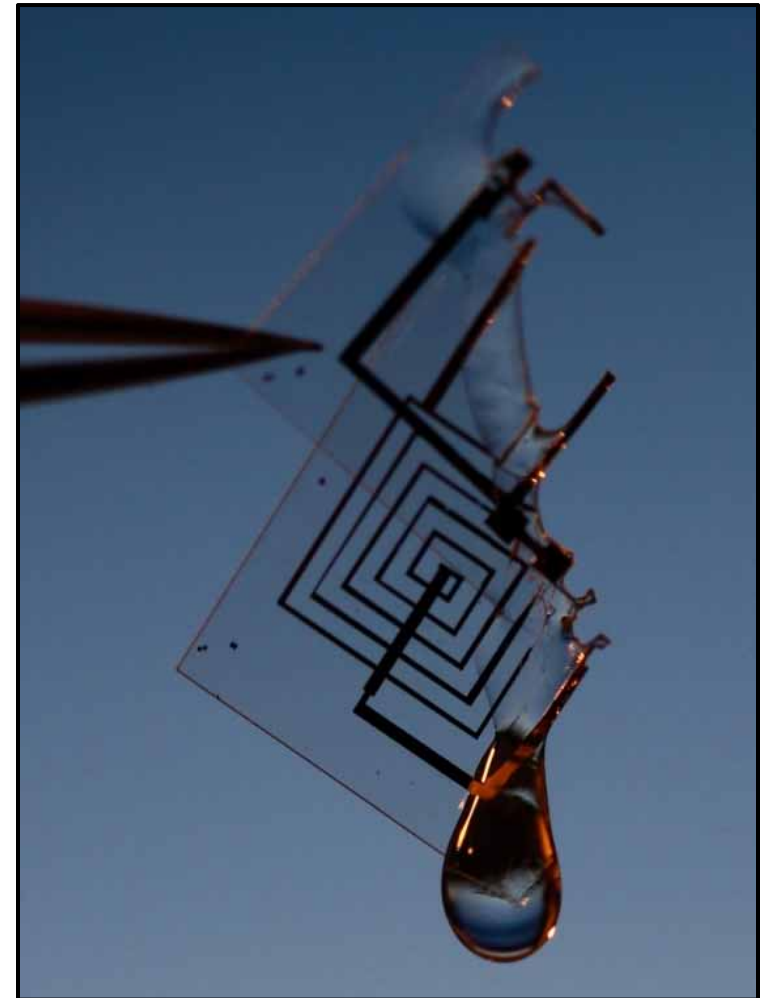
Clinical Medicine

Prof. I. Efimov (GWU) – cardiac

Prof. R. Murphy (WU) -- TBI

Prof. Z. Ray (WU) – neuroregen

Prof. M. MacEwan (WU) -- regen



Research Team

